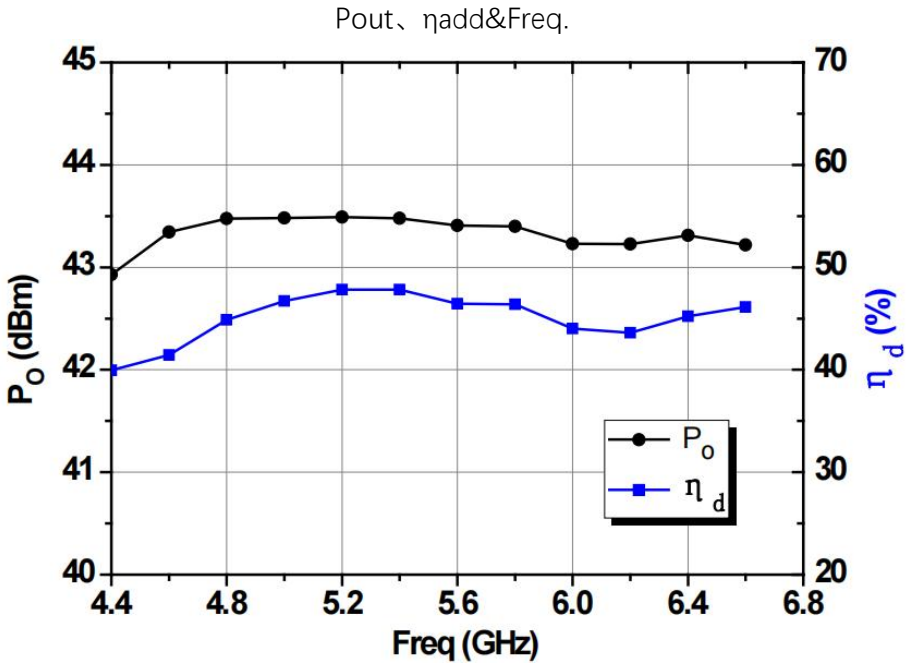
Performance

- Technology: 0.25um Power GaN HEMT
- Frequency: 4.4~6.6GHz
- Typical Pout : ≧43dBm(CW)
- Typical Gain: ≧8dB
- Typical PAE: ≧40%
- Bias: 28V@0.3A
- Package: Metal Ceramic

Electrical Specifications（TA=25℃,Vd=28V,Idq=0.3A,F: 4.4~6.6GHz,Pin=35dBm）

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	43	-	-	dBm
Gp	Power Gain	8	-	-	dB
ηadd	Power Added Efficiency	40	-	-	%
△Gp	Gain Flatness	-	-	±0.3	dB

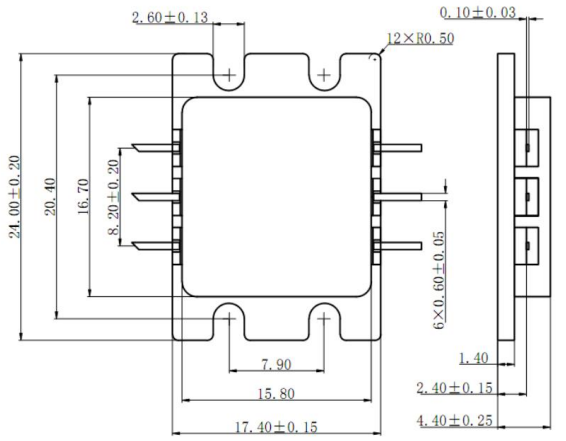
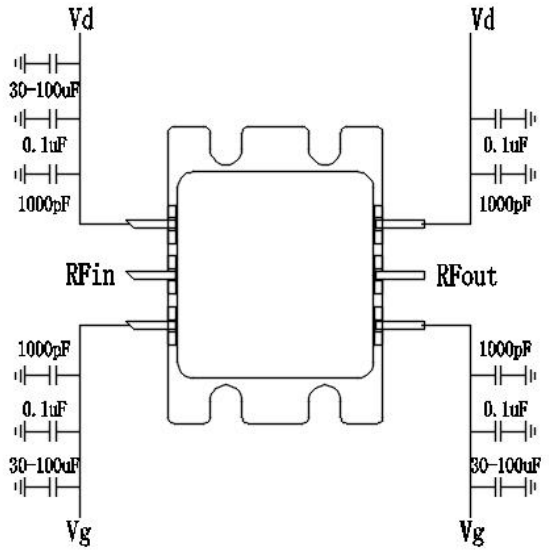
Test Curves



Absolute Max Ratings (T_A=25℃)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	40V	
Vg	Grid Voltage	-5V	
Pd	DC Dissipation	75W	25℃
Tch	Channel Temperature	225℃	【1】
Tm	Mounting Temperature	300℃	1 min, N_2 Protection
Tstg	Storage Temperature	-55~175℃	

【1】Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing	Application Circuit
	

Note:

(1) This product is an internally matched power transistor with input and output impedance values of 50 ohms;

(2) Please strictly follow the sequence of applying negative power first and then positive power. When removing power, first decrease the leakage voltage and then decrease the gate voltage;

(3) This product is a high-power device, and attention should be paid to heat dissipation during use. The higher the shell temperature, the shorter the service life, and the appropriate use temperature should not be higher than 85 degrees Celsius;

(4) This product is an electrostatic sensitive device, which requires attention to electrostatic protection during storage and use, and requires good grounding during use;

(5) The input standing wave ratio is high, and the input terminal needs to adopt radio frequency isolation measures.